

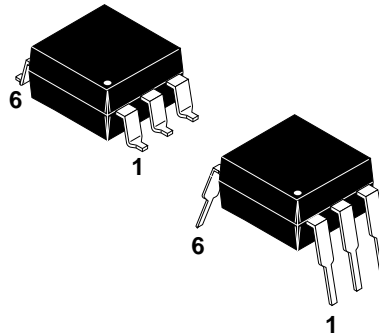
## DESCRIPTION

The CNW82, CNW83, CNW84 and CNW85 optocouplers consist of a GaAs infrared emitting diode which is optically coupled to an NPN phototransistor.

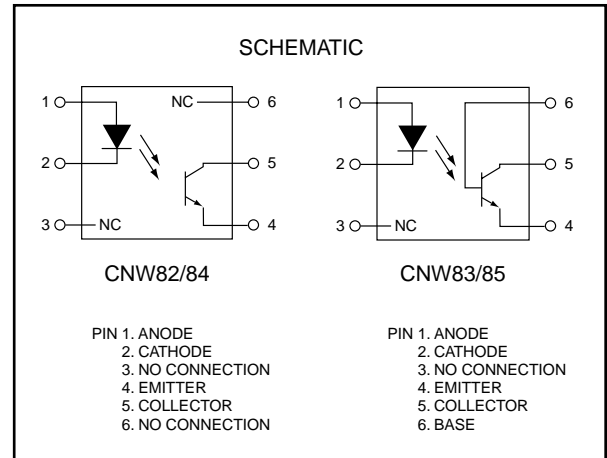
The CNW82 and CNW84 do not have the base pin connected for improved noise immunity.

## FEATURES

- Wide body DIL encapsulation, with a pin distance of 10.16 mm.
- Minimum creepage distance 10 mm.
- High current transfer ratio and Low Saturation Voltage, making the device suitable for use with TTL integrated circuits.
- High degree of AC and DC insulation (5900 V (RMS) and 8340 V (DC)).
- Minimum 2 mm isolation thickness between emitter and detector. (CNW84/85 only).
- An external clearance of 9.6 mm minimum and an external creepage distance of 10 mm minimum.
- Collector-Emitter Breakdown Voltage: 50 V (CNW82/83 only).
- Collector-Emitter Breakdown Voltage: 80 V (CNW84/85 only).
- UL recognized (File # E90700)



CNW82  
 CNW83  
 CNW84  
 CNW85



<b>ABSOLUTE MAXIMUM RATINGS</b>			
Parameter	Symbol	Value	Units
<b>EMITTER</b>			
Forward Current - Continuous	$I_F$	100	mA
Forward Current - Peak (PW = 100µs, 120pps)	$I_F(pk)$	3	A
Reverse Voltage	$V_R$	5	V
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	200	mW
Derate above 25°C		2.0	mW/°C
<b>DETECTOR</b>			
Collector Current-Continuous	$I_C$	100	mA
Emitter-Collector Voltage	$V_{ECO}$	7	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
(CNW82/CNW83)		80	
Collector-Base Voltage	$V_{CBO}$	70	V
(CNW85)		120	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	200	mW
Derate above 25°C		2.0	mW/°C
<b>TOTAL DEVICE</b>			
Storage Temperature Range	$T_{stg}$	-55 to 150	°C
Ambient Operating Temperature Range	$T_A$	-40 to 100	°C
Lead Soldering Temperature (1/16" from case, 10 sec. duration)	$T_L$	260	°C

**CNW82, CNW83, CNW84, CNW85**

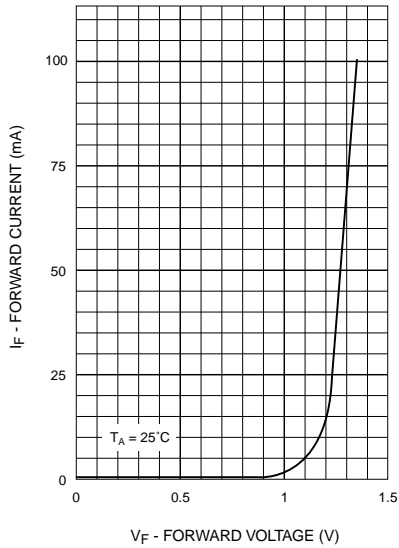
<b>ELECTRICAL CHARACTERISTICS</b> ( $T_A = 25^\circ\text{C}$ Unless otherwise specified)						
Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
<b>EMITTER</b>						
Input Forward Voltage	( $I_F = 10\text{ mA}$ )	$V_F$	—	1.20	1.50	V
Reverse Leakage Current	( $V_R = 5.0\text{ V}$ )	$I_R$	—	—	10	$\mu\text{A}$
<b>DETECTOR</b>						
Collector-Emitter Breakdown Voltage	( $I_C = 1.0\text{ mA}$ )	$BV_{CEO}$	50	100	—	V
Emitter-Collector Breakdown Voltage	( $I_E = 0.1\text{ mA}$ )	$BV_{ECO}$	7	10	—	V
Collector-Base Breakdown Voltage	( $I_C = 0.1\text{ mA}$ )	$BV_{CBO}$	70	100	—	V
Collector-Emitter Dark Current	( $V_{CE} = 10\text{ V}, I_F = 0$ )	$I_{CEO}$	—	1	50	nA
Collector-Base Cut-off Current	( $V_{CB} = 10\text{ V}, I_F = 0$ )	$I_{CBO}$	—	—	20	nA
<b>COUPLED</b>						
Collector-Emitter Saturation Voltage	( $I_C = 4\text{ mA}, I_F = 10\text{ mA}$ )	$V_{CE(sat)}$	—	0.15	0.4	V
Isolation Voltage	(DC Value) (t = 1.0 min.) <sup>(1)</sup> (RMS Value) (t = 1.0 min.) <sup>(1)</sup>	$V_{ISO}$	8.34	—	—	kV
Isolation Resistance	( $V_{I-O} = 500\text{ V}$ )	$R_{ISO}$	1	10	—	$\text{T}\Omega$
Isolation Capacitance	( $V_{I-O} = 0, f = 1.0\text{ MHz}$ )	$C_{ISO}$	—	0.4	1	pF
Current Transfer Ratio	( $I_F = 10\text{ mA}, V_{CE} = 0.4\text{ V}$ ) ( $I_F = 10\text{ mA}, V_{CE} = 5\text{ V}$ )	CTR	0.4	0.8	—	%
Capacitance	( $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$ )	$C_{CB}$	—	4.5	—	pF
Turn-on Time	( $I_C = 2\text{ mA}, V_{CC} = 5\text{ V}, R_L = 100\ \Omega$ ) ( $I_C = 2\text{ mA}, V_{CC} = 5\text{ V}, R_L = 1\text{ k}\Omega$ )	$T_{ON}$	—	3	—	$\mu\text{s}$
Turn-off Time	( $I_C = 2\text{ mA}, V_{CC} = 5\text{ V}, R_L = 100\ \Omega$ ) ( $I_C = 2\text{ mA}, V_{CC} = 5\text{ V}, R_L = 1\text{ k}\Omega$ )	$T_{OFF}$	—	3	—	$\mu\text{s}$

**NOTE:**

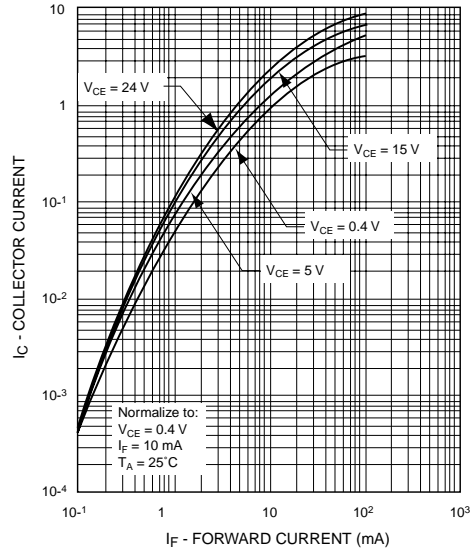
1. Every product is tested with pins 1, 2 and 3 shorted together, and pins 4, 5 and 6 shorted together.

**CNW82, CNW83, CNW84, CNW85**

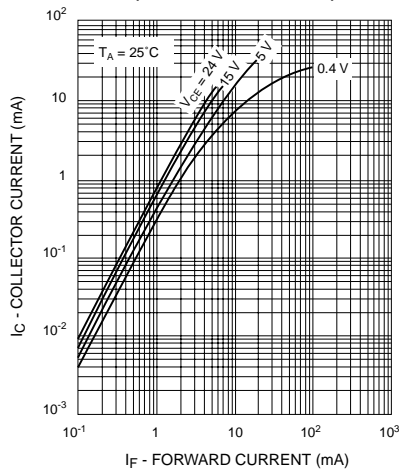
**Fig. 1 Forward Current vs. Forward Voltage**



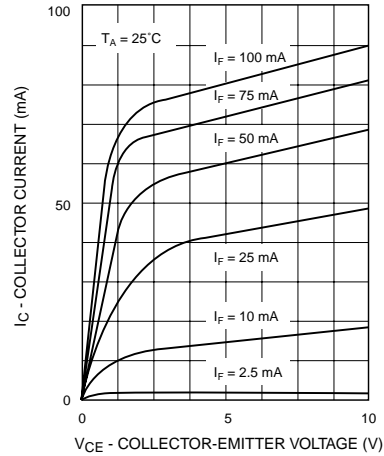
**Fig. 2 Collector Current vs. Forward Current (for CNW84 and CNW85)**



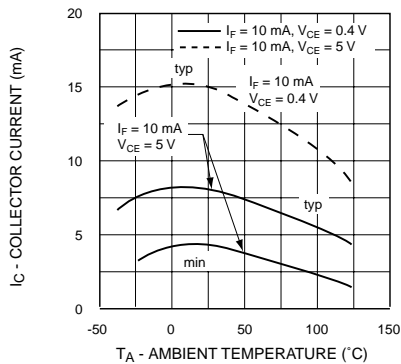
**Fig. 3 Collector Current vs. Forward Current (for CNW82 and CNW83)**



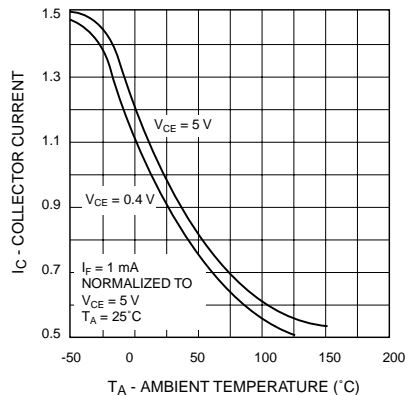
**Fig. 4 Collector Current vs. Collector-Emitter Voltage**



**Fig. 5 Collector Current vs. Ambient Temperature (for CNW82 and CNW83)**

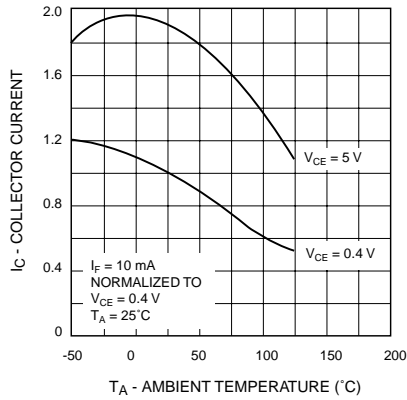


**Fig. 6 Collector Current vs. Ambient Temperature (for CNW84 and CNW85)**

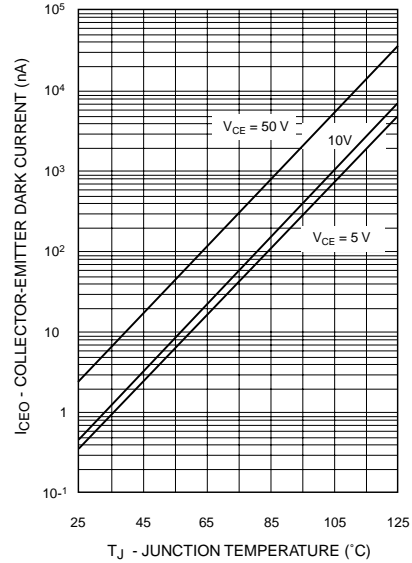


**CNW82, CNW83, CNW84, CNW85**

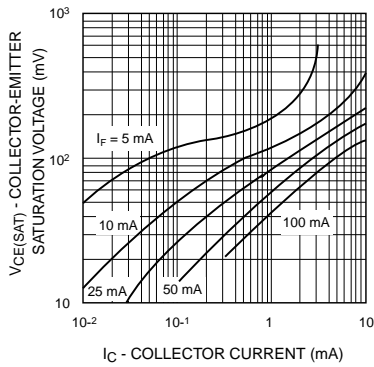
**Fig. 7 Collector Current vs. Ambient Temperature  
(for CNW84 and CNW85)**



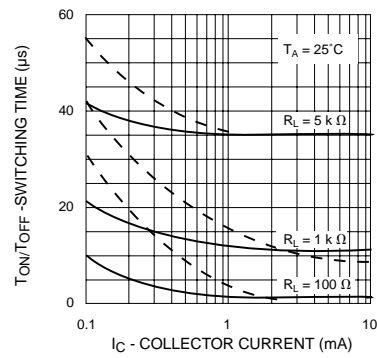
**Fig. 8 Collector-Emitter Dark Current vs. Junction Temperature**



**Fig. 9 Collector-Emitter Saturation Voltage vs. Collector Current**

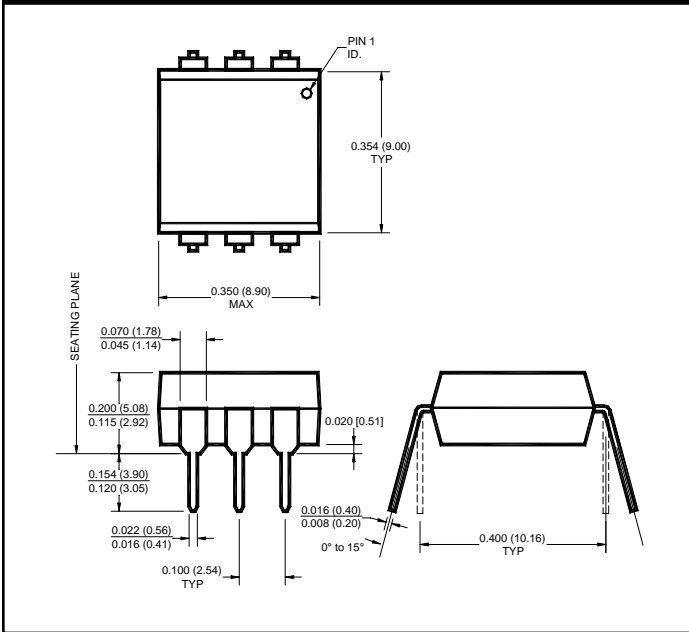


**Fig. 10 Rise and Fall Time vs. Collector Current**

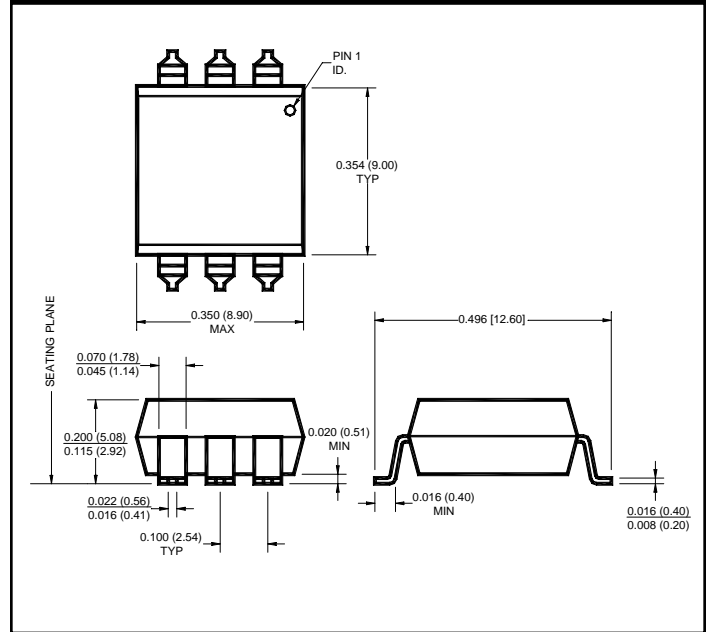


**CNW82, CNW83, CNW84, CNW85**

**Package Dimensions (Through Hole)**



**Package Dimensions (Surface Mount)**



**NOTE**

All dimensions are in inches (millimeters)

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